

FileViewEditToolsWindowHelp

Active

L1: (155) (((cell memory) near2 (area region section portion D

L2: (100531) cmos

L3: (94) 1 and 2

L4: (22678) pmos with nmos

L5: (70) 3 and 4

L6: (110) (257/214) CCLS

Failed

Saved

(1) 08/948877

(1736) "KONINKLLIKE PHILIPS".as

(2) 10/253779

(1) 10/234501

(37717) n-well pmos

(43184) p-well nmos

(1978052) peripher\$2 logic

(2357117) cell memory

(182171) (peripher\$2 logic 0) with (cell memory)

(3810307) region area

(82488) (cell memory) adj2 (region area)

(7362802) (area region section portion)

(215405) (cell memory) near2 (area region section portion D)

(270282) (peripher\$2 logic 0) near2 (area region section portion D)

(809848) polysilicon poly adj silicon silicon

(3102552) metal

BrowseQueueClear

DBs:USPAT,USPGPUB,EPO,JPO,DERWENT,ICOM,TDD

Default operator:OR

P:Plurals

P:Highlight all hit terms initially

10/253779

Feb. 2 2004

US 2003008 20030:2 CMOS of semiconductor device and method f 257/369:257/E21.63

US 6642132 20031:2 Cmos of semiconductor device and method f 438/592:257/315

Ready